
2SC4050

Silicon NPN Epitaxial

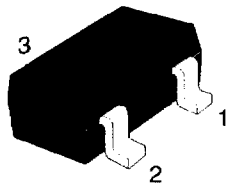
HITACHI

Application

Low frequency amplifier, switching

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

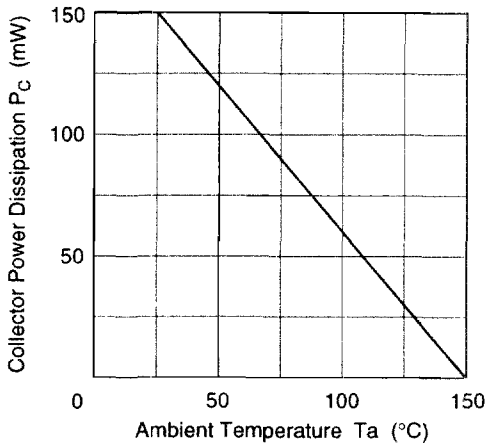
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 70 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}^{*2}$

Notes: 1. The 2SC4050 is grouped by h_{FE} as follows.

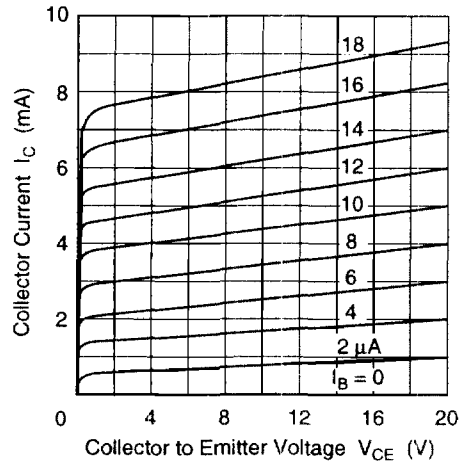
2. Pulse test

Grade	D	E
Mark	KID	KIE
h_{FE}	250 to 500	400 to 800

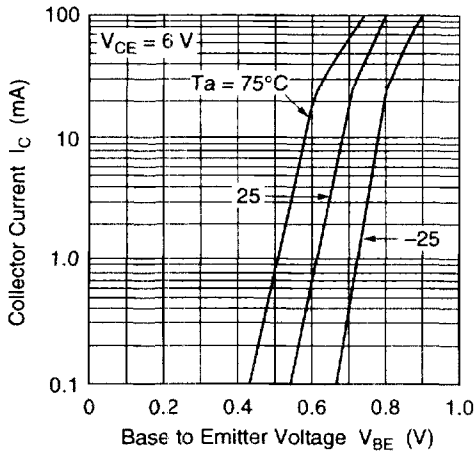
Maximum Collector Dissipation Curve



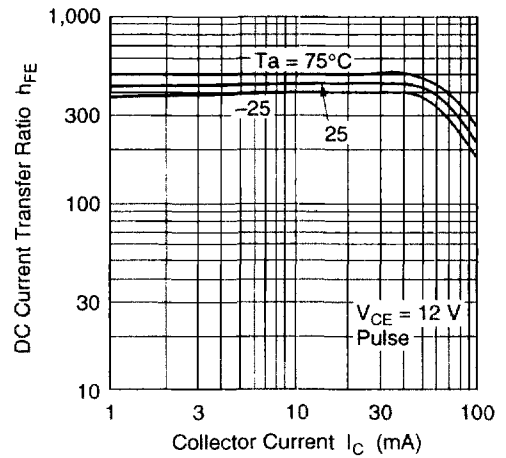
Typical Output Characteristics



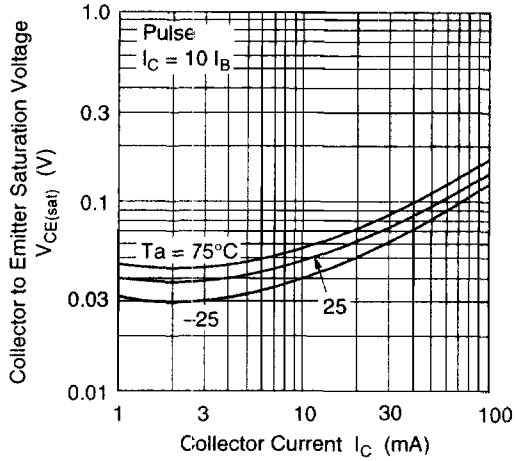
Typical Transfer Characteristics



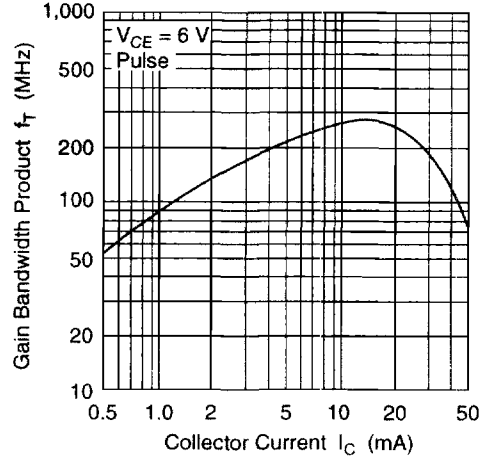
DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



Gain Bandwidth Product vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage

